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MOC256M
8-pin SOIC AC Input Phototransistor Output Optocoupler

Features

- Bidirectional AC Input
  - Protection Against Reversed DC Bias
- Guaranteed CTR Symmetry of 2:1 Maximum
- Convenient Plastic SOIC-8 Surface Mountable Package Style, with 0.050" Lead Spacing
- Safety and Regulatory Approvals:
  - UL1577, 2,500 VAC_{RMS} for 1 Minute
  - DIN-EN/IEC60747-5-5, 565 V Peak Working Insulation Voltage

Description

The MOC256M is an AC input phototransistor opto-coupler. The device consists of two infrared emitters connected in anti-parallel and coupled to a silicon NPN phototransistor detector. It is designed for applications requiring the detection or monitoring of AC signals. The device is constructed with a standard SOIC-8 footprint.

Schematic

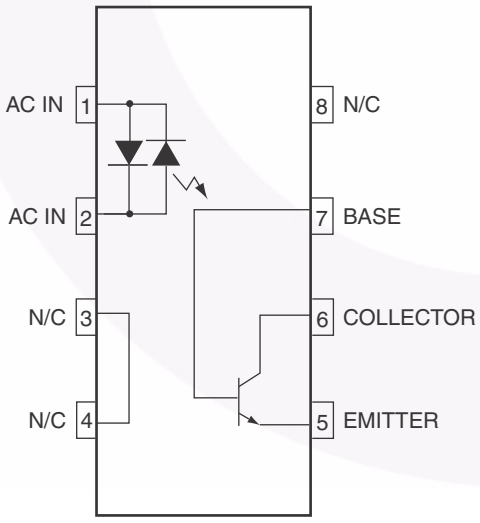


Figure 1. Schematic

Package Outline

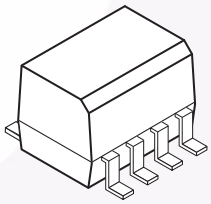


Figure 2. Package Outline

Safety and Insulation Ratings

As per DIN EN/IEC 60747-5-5, this optocoupler is suitable for “safe electrical insulation” only within the safety limit data. Compliance with the safety ratings shall be ensured by means of protective circuits.

Parameter		Characteristics
Installation Classifications per DIN VDE 0110/1.89 Table 1, For Rated Mains Voltage	< 150 V_{RMS}	I–IV
	< 300 V_{RMS}	I–III
Climatic Classification		55/100/21
Pollution Degree (DIN VDE 0110/1.89)		2
Comparative Tracking Index		175

Symbol	Parameter	Value	Unit
V_{PR}	Input-to-Output Test Voltage, Method A, V_{IORM} x 1.6 = V_{PR}, Type and Sample Test with t_m = 10 s, Partial Discharge < 5 pC	904	V_{peak}
	Input-to-Output Test Voltage, Method B, V_{IORM} x 1.875 = V_{PR}, 100% Production Test with t_m = 1 s, Partial Discharge < 5 pC	1060	V_{peak}
V_{IORM}	Maximum Working Insulation Voltage	565	V_{peak}
V_{IOTM}	Highest Allowable Over-Voltage	4000	V_{peak}
	External Creepage	≥ 4	mm
	External Clearance	≥ 4	mm
DTI	Distance Through Insulation (Insulation Thickness)	≥ 0.4	mm
T_S	Case Temperature(1)	150	°C
$I_{S,INPUT}$	Input Current(1)	200	mA
$P_{S,OUTPUT}$	Output Power(1)	300	mW
R_{IO}	Insulation Resistance at T_S, V_{IO} = 500 V(1)	> 10^9	Ω

Note:

1. Safety limit values – maximum values allowed in the event of a failure.

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. T_A = 25°C unless otherwise specified.

Symbol	Rating	Value	Unit
TOTAL DEVICE			
T_{STG}	Storage Temperature	-40 to +125	°C
T_A	Ambient Operating Temperature	-40 to +100	°C
T_J	Junction Temperature	-40 to +125	°C
T_{SOL}	Lead Solder Temperature	260 for 10 seconds	°C
P_D	Total Device Power Dissipation @ T_A = 25°C	240	mW
	Derate Above 25°C	2.94	mW/°C
EMITTER			
I_F	Continuous Forward Current	60	mA
I_F (pk)	Forward Current – Peak (PW = 100 µs, 120 pps)	1.0	A
V_R	Reverse Voltage	6.0	V
P_D	LED Power Dissipation @ T_A = 25°C	90	mW
	Derate Above 25°C	0.8	mW/°C
DETECTOR			
I_C	Continuous Collector Current	150	mA
V_{CEO}	Collector-Emitter Voltage	30	V
V_{CBO}	Collector-Base Voltage	70	V
V_{ECO}	Emitter-Collector Voltage	7	V
P_D	Detector Power Dissipation @ T_A = 25°C	150	mW
	Derate Above 25°C	1.76	mW/°C

Electrical Characteristics

T_A = 25°C unless otherwise specified.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
EMITTER						
V_F	Input Forward Voltage	I_F = ±10 mA		1.2	1.5	V
C_{IN}	Input Capacitance	V = 0 V, f = 1 MHz		20		pF
DETECTOR						
I_{CEO1}	Collector-Emitter Dark Current	V_{CE} = 10 V, T_A = 25°C		1.0	100	nA
I_{CEO2}		V_{CE} = 10 V, T_A = 100°C		1.0		µA
I_{CBO}	Collector-Base Dark Current	V_{CB} = 10 V		0.2		nA
BV_{CEO}	Collector-Emitter Breakdown Voltage	I_C = 10 mA	30	100		nA
BV_{CBO}	Collector-Base Breakdown Voltage	I_C = 100 µA	70	120		V
BV_{ECO}	Emitter-Collector Breakdown Voltage	I_E = 100 µA	5	10		V
C_{CE}	Collector-Emitter Capacitance	f = 1.0 MHz, V_{CE} = 0		7		pF
C_{CB}	Collector-Base Capacitance	f = 1.0 MHz, V_{CB} = 0		20		pF
C_{EB}	Emitter-Base Capacitance	f = 1.0 MHz, V_{EB} = 0		10		pF
COUPLED						
CTR	Current Transfer Ratio	I_F = ±10 mA, V_{CE} = 10 V	20	150		%
	Output-Collector Current Symmetry	$\left(\frac{I_C \text{ @ } I_F = +10 \text{ mA}, V_{CE} = 10 \text{ V}}{I_C \text{ @ } I_F = -10 \text{ mA}, V_{CE} = 10 \text{ V}}\right)$	0.5		2.0	
$V_{CE\ (SAT)}$	Collector-Emitter Saturation Voltage	I_C = 0.5 mA, I_F = ±10 mA		0.1	0.4	V

Isolation Characteristics

Symbol	Characteristic	Test Conditions	Min.	Typ.	Max.	Unit
V_{ISO}	Input-Output Isolation Voltage	t = 1 Minute	2500			VAC_{RMS}
C_{ISO}	Isolation Capacitance	V_{I-O} = 0 V, f = 1 MHz		0.2		pF
R_{ISO}	Isolation Resistance	V_{I-O} = ±500 VDC, T_A = 25°C	10^{11}			Ω

Typical Performance Curves

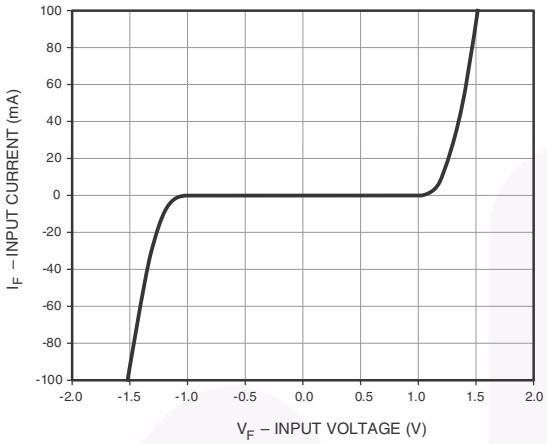


Figure 3. Input Current vs. Input Voltage

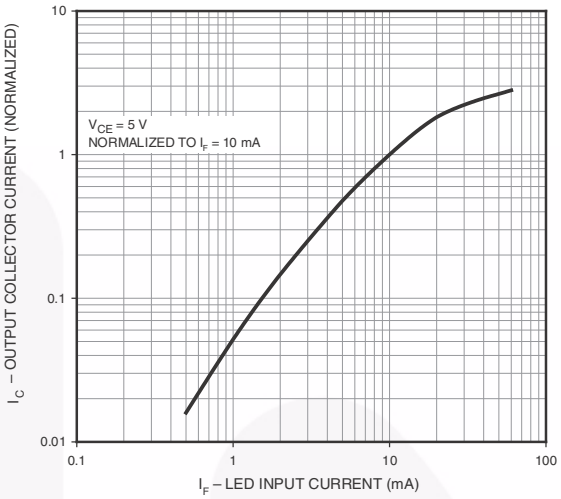


Figure 4. Output Curent vs. Input Current

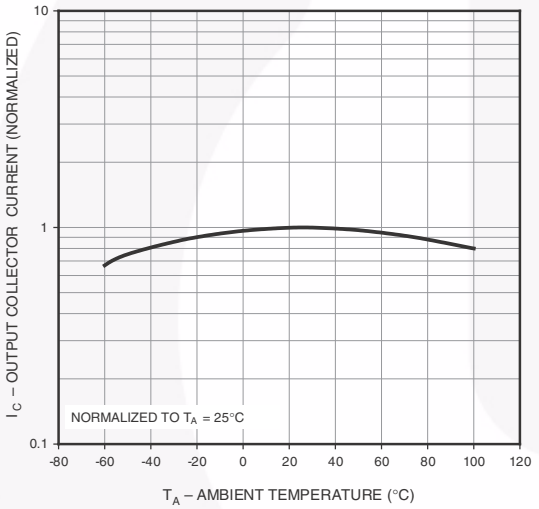


Figure 5. Output Current vs. Ambient Temperature

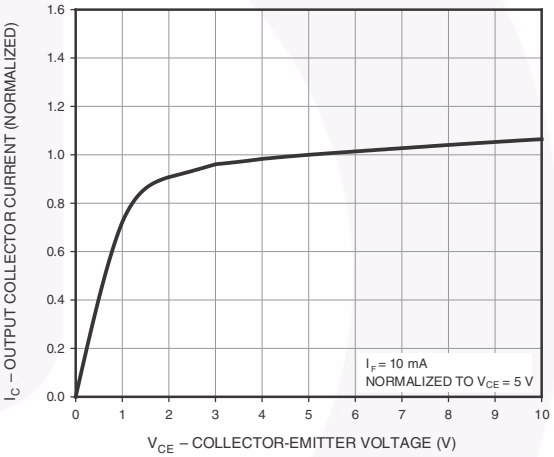


Figure 6. Output Current vs. Collector-Emitter Voltage

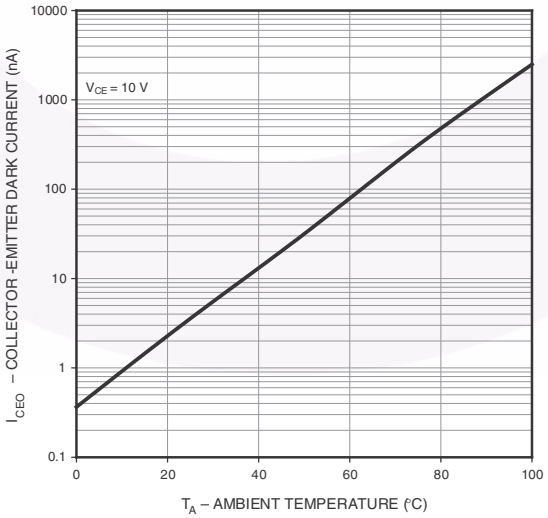


Figure 7. Dark Current vs. Ambient Temperature

Reflow Profile

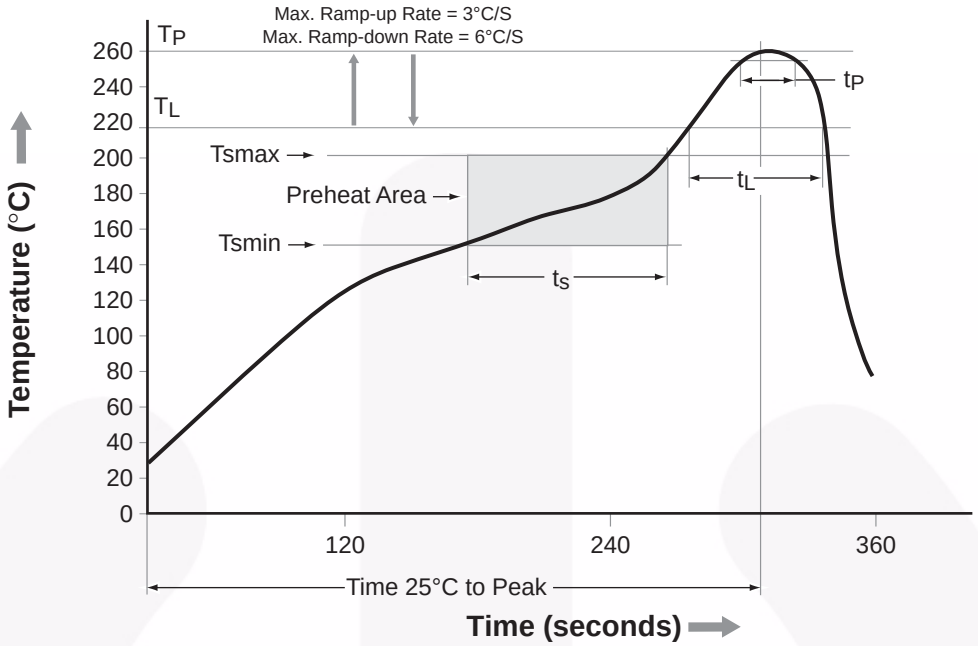


Figure 8. Reflow Profile

Profile Freature	Pb-Free Assembly Profile
Temperature Minimum (Tsmin)	150°C
Temperature Maximum (Tsmax)	200°C
Time (t_S) from (Tsmin to Tsmax)	60–120 seconds
Ramp-up Rate (t_L to t_P)	3°C/second maximum
Liquidous Temperature (T_L)	217°C
Time (t_L) Maintained Above (T_L)	60–150 seconds
Peak Body Package Temperature	260°C +0°C / –5°C
Time (t_P) within 5°C of 260°C	30 seconds
Ramp-down Rate (T_P to T_L)	6°C/second maximum
Time 25°C to Peak Temperature	8 minutes maximum

Ordering Information

Part Number	Package	Packing Method
MOC256M	Small Outline 8-Pin	Tube (100 Units)
MOC256R2M	Small Outline 8-Pin	Tape and Reel (2500 Units)
MOC256VM	Small Outline 8-Pin, DIN EN/IEC60747-5-5 Option	Tube (100 Units)
MOC256R2VM	Small Outline 8-Pin, DIN EN/IEC60747-5-5 Option	Tape and Reel (2500 Units)

Marking Information

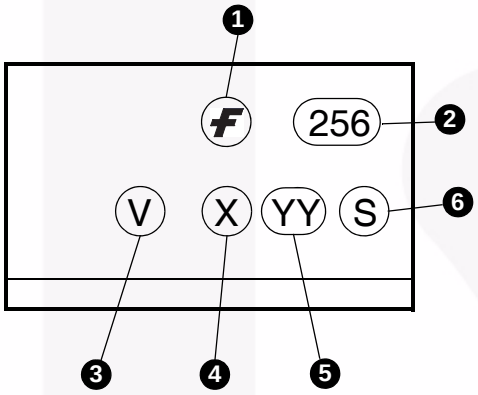
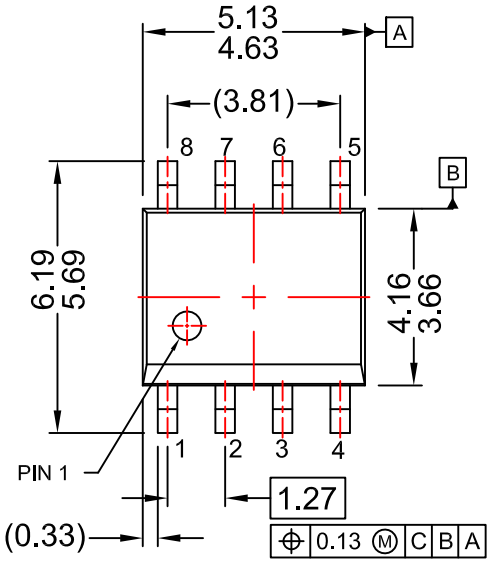
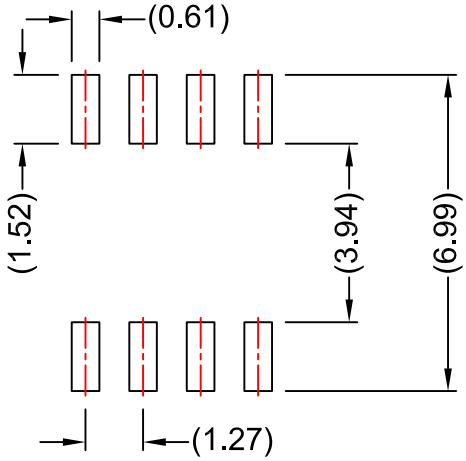


Figure 9. Top Mark

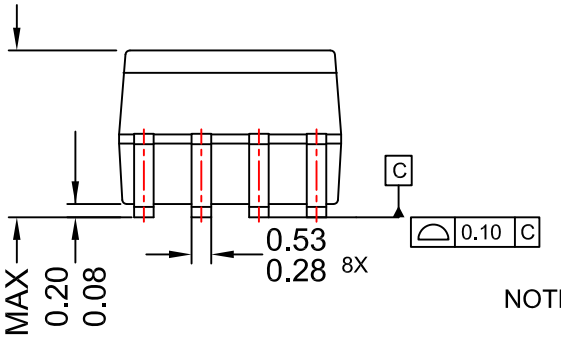
Table 1. Top Mark Definitions

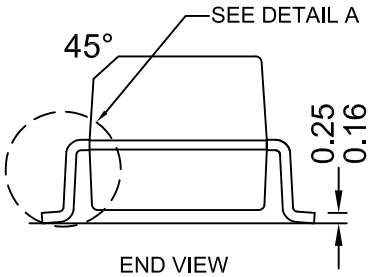
1	Fairchild Logo
2	Device Number
3	DIN EN/IEC60747-5-5 Option (only appears on component ordered with this option)
4	One-Digit Year Code, e.g., “4”
5	Digit Work Week, Ranging from “01” to “53”
6	Assembly Package Code



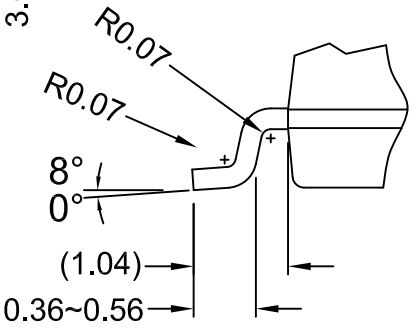


LAND PATTERN RECOMMENDATION





END VIEW



DETAIL A
SCALE: 2:1

NOTES:

A) NO STANDARD APPLIES TO THIS PACKAGE
B) ALL DIMENSIONS ARE IN MILLIMETERS.
C) DIMENSIONS DO NOT INCLUDE MOLD FLASH OR BURRS.
D) LANDPATTERN STANDARD: SOIC127P600X175-8M.
E) DRAWING FILENAME: MKT-M08Erev5

FAIRCHILD

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